

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

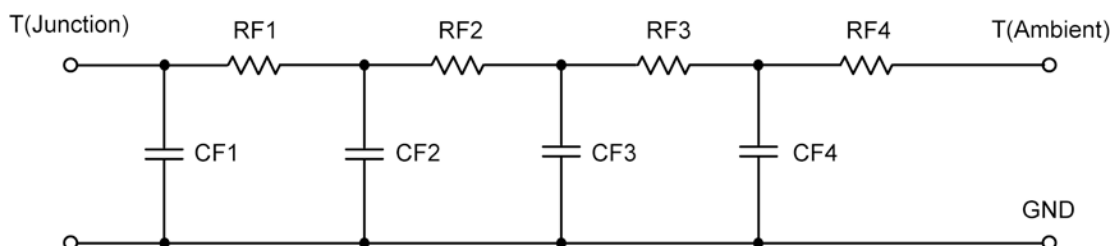
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	10.2698	N/A	7.5124
RT2	32.1014	N/A	6.2331
RT3	18.2159	N/A	15.1701
RT4	49.4129	N/A	9.0844
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	214.6398 u	N/A	11.0242 m
CT2	3.8620 m	N/A	153.3919 u
CT3	105.7563 m	N/A	1.1849 m
CT4	1.6050	N/A	13.5787 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	9.6801	N/A	8.6355
RF2	31.8644	N/A	18.9290
RF3	18.5606	N/A	9.0152
RF4	49.8949	N/A	1.4203
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	160.7755 u	N/A	136.1155 u
CF2	2.9127 m	N/A	1.0726 m
CF3	55.8395 m	N/A	5.8469 m
CF4	1.4156	N/A	454.8802 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

